

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

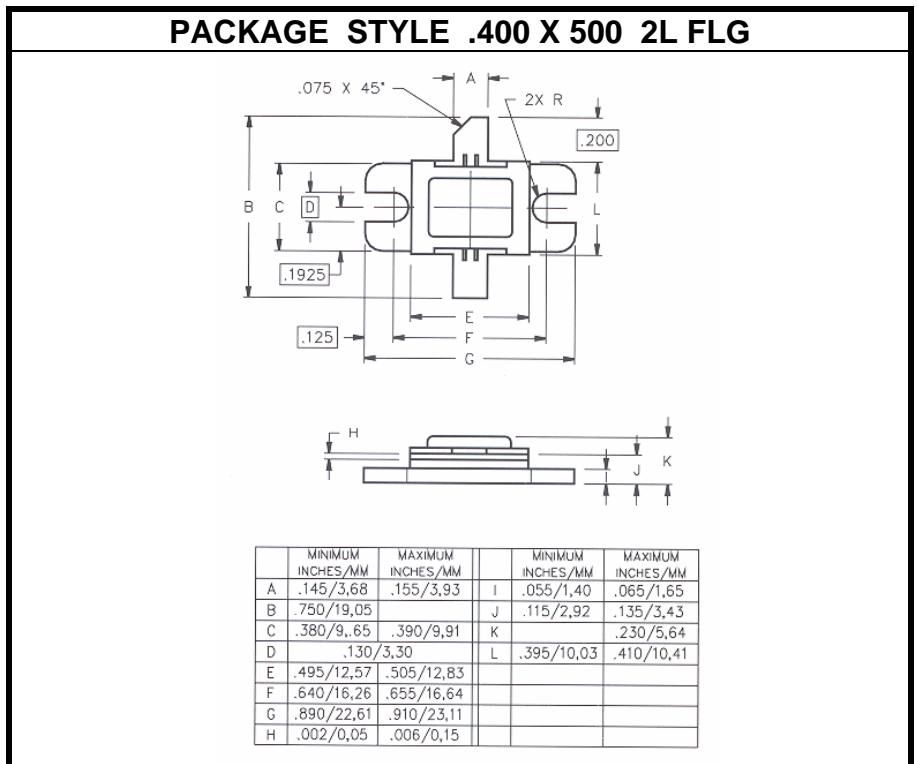
The **ASI SD1542-42** is a Common Base Device Designed for, IFF and DME Pulse Applications.

FEATURES INCLUDE:

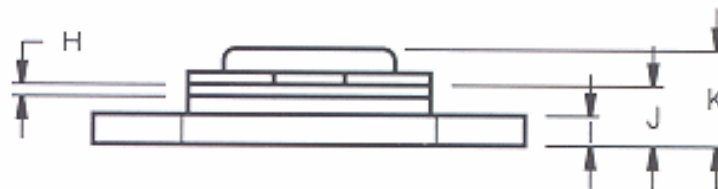
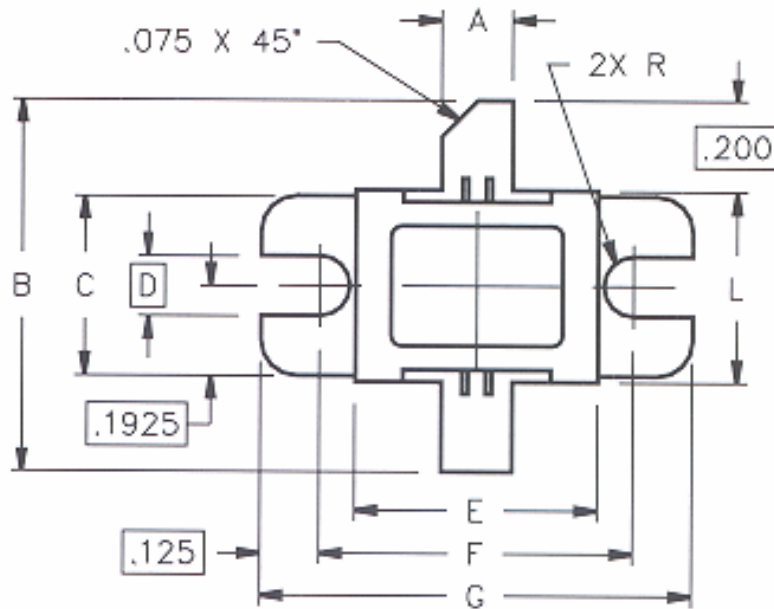
- Gold Metalization
- Input/Output Matching
- Hermetically Sealed

MAXIMUM RATINGS

I_C	45 A
V_{CC}	55 V
P_{DISS}	1670 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.06 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 25 mA	65			V
BV_{CER}	I _C = 25 mA R _{BE} = 10 Ω	65			V
BV_{EBO}	I _E = 10 mA	3.5			V
I_{CES}	V _{CE} = 50 V			60	mA
h_{FE}	V _{CE} = 5.0 V I _C = 2.0 A	10		250	---
P_G	V _{CC} = 50 V P _{IN} = 150 W f = 1090 MHz PULSE	6.0	6.6		dB
η_C	WIDTH = 10 μS DUTY CYCLE = 1.0%	35	40		%
P_{OUT}		600	680		W



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.145/3,68	.155/3,93	I	.055/1,40	.065/1,65
B	.750/19,05		J	.115/2,92	.135/3,43
C	.380/9,65	.390/9,91	K		.230/5,64
D	.130/3,30		L	.395/10,03	.410/10,41
E	.495/12,57	.505/12,83			
F	.640/16,26	.655/16,64			
G	.890/22,61	.910/23,11			
H	.002/0,05	.006/0,15			